

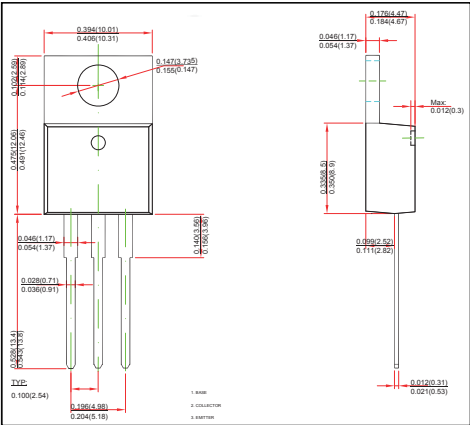
TO-220-3L Plastic-Encapsulate Transistors

FEATURES

- High Current Switching Applications
- Low Collector Saturation Voltage
- High Speed Switching Time
- TRANSISTOR (PNP)

MECHANICAL DATA

- Case style:TO-220-3Lmolded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	-60	V
Collector-Emitter Voltage	V _{CEO}	-50	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current -Continuous	I _C	-5	A
Collector Power Dissipation	P _C	2	W
Thermal Resistance Junction to Ambient	R _{θJA}	62.5	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	-55~+150	°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -0.1mA, I _E = 0	-60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -10mA, I _B = 0	-50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -100µA, I _C = 0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} = -50V, I _E = 0			-1	µA
Emitter cut-off current	I _{EBO}	V _{EB} = -5V, I _C = 0			-1	µA
DC current gain	h _{FE(1)}	V _{CE} = -1V, I _C = -1A	70		24	
	h _{FE(2)}	V _{CE} = -1V, I _C = -3A	30			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -3A, I _B = -150mA			-0.4	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = -3A, I _B = -150mA			-1.2	V
Transition frequency	f _T	V _{CE} = -4V, I _C = -1A		60		MHz
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f = 1MHz		170		pF
Turn-on Time	t _{on}	V _{CC} = -30V, I _C = -3A, I _{B1} = -I _{B2} = -0.15A		0.1		µs
Storage Time	t _s		1.0			
Fall Time	t _f		0.1			

*Pulse test: t_p ≤ 300µs, δ ≤ 0.02